

AMENDMENTS TO THE SPECIFICATION

Page 1, line 19 through Page 2, line 6, please amend as follows:

The ECR plasma source comprises a plasma generating chamber, a magnetic coil and a microwave introducing portion. The ECR sputtering or etching device of the prior art has been intended mainly for a wafer-shaped circular sample placed still. Therefore, the ECR plasma source for those device comprises: a plasma generating chamber having a circular sectional shape in a plane normal to a plasma flow; a magnetic coil wound to have a circular sectional shape in a plane normal to the plasma flow; and a microwave introducing portion having a structure for introducing the microwaves either directly or in a branching and binding method from a microwave waveguide (as referred to Japanese Patent No. 1553959 Japanese Patent Application Publication No. 01-036693 (1989) (Japanese Patent No. 1553959) or "Deposition of High Quality Thin Films Using ECR Plasma" by Amazawa et al., Reports of Precision Engineering Society Vol. 66, No. 4, 511 (2001) (2000).

Page 20, line 27 through page 21, line 6, please amend as follows:

According to the invention, still moreover, the ECR plasma device comprises not only the aforementioned ECR plasma source as the plasma source but also the sample moving mechanism for moving the large-sized sample. It is possible to provide the ECR plasma device which can sputter or etch even the large-sized sample of the generally rectangular shape such as the FPD easily.